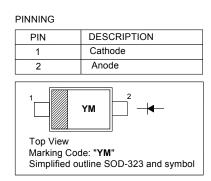
SILICON EPITAXIAL PLANAR DIODE

High Voltage Switching Diode

Features

- Fast switching speed
- High conductance
- High reverse breakdown voltage rating



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	400	V
Reverse Voltage	V _R	350	V
Continuous Forward Current	١ _F	225	mA
Repetitive Peak Forward Current	I _{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current (1 ms)	I _{FSM}	2	А
Power Dissipation	P _d	350	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	- 65 to + 150	°C

Characteristics at T_a = 25 °C

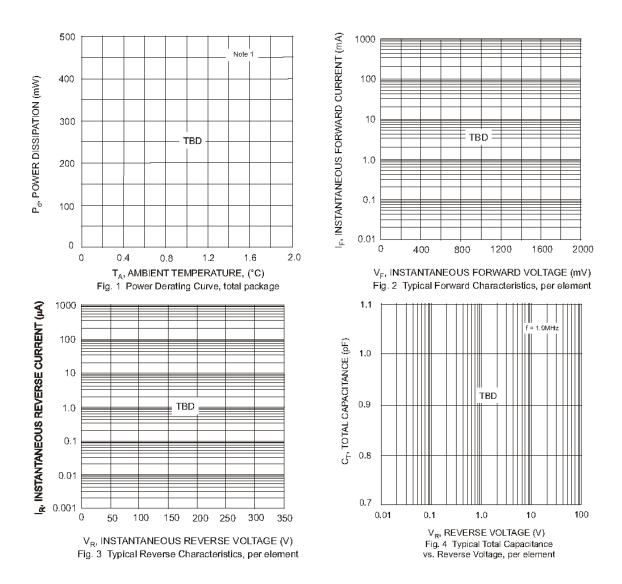
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 20 \text{ mA}$ at $I_F = 100 \text{ mA}$ at $I_F = 200 \text{ mA}$	V _F	- -	0.87 1 1.25	V
Reverse Current at V_R = 240 V	I _R	-	100	nA
Reverse Breakdown Voltage at I _R = 150 μA	V _{(BR)R}	400	-	V
Total Capacitance at $V_R = 0$, f = 1 MHz	CT	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30 \text{ mA}$, $i_{rr} = 3 \text{ mA}$, $R_L = 100 \Omega$	t _{rr}	-	100	ns







Dated : 15/03/2008







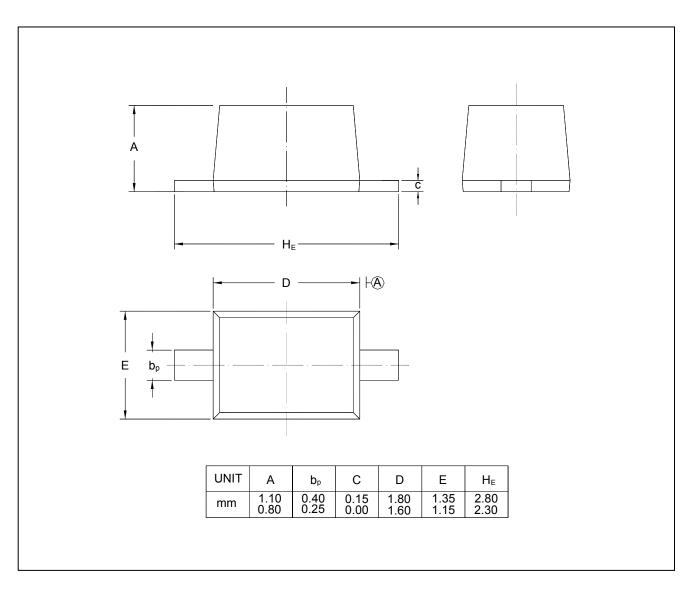


Dated : 15/03/2008

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323









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